

TO-92 Plastic-Encapsulate Transistors

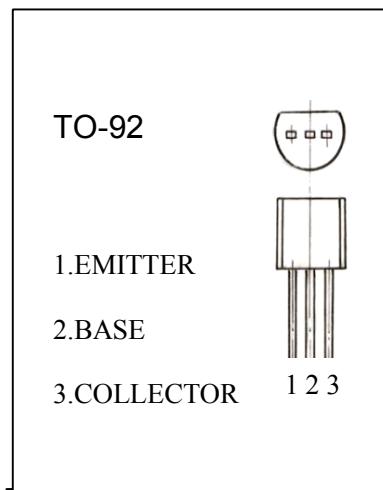
FEATURES

Power dissipation

PC : 1 W (TA=25°C)

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-40	V
VCEO	Collector-Emitter Voltage	-25	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current-Continuous	-1.5	A
Tj	Junction Temperature	150	°C
Tstg	Storage Temperature	-55-150	°C



CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-0.1mA, IB=0	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-40V, IE=0			-0.1	μA
Emitter cut-off current	ICEO	VCE=-20V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0			-0.1	uA
DC current gain	hFE(1)	VCE=-1V, IC=-100mA	85		400	
	hFE(2)	VCE=-1V, IC=-800mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=-800mA, IB=-80mA			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-800mA, IB=-80mA			-1.2	V
Base-emitter voltage	VBE(on)	VCE=-1V, IC=-10mA			-1	V
Out capacitance	Cob	VCB=-10V, IE=0mA, f=1MHZ			20	pF
Transition frequency	fT	VCE=-10V, IC=-50mA, f=-30MHZ	100			MHZ

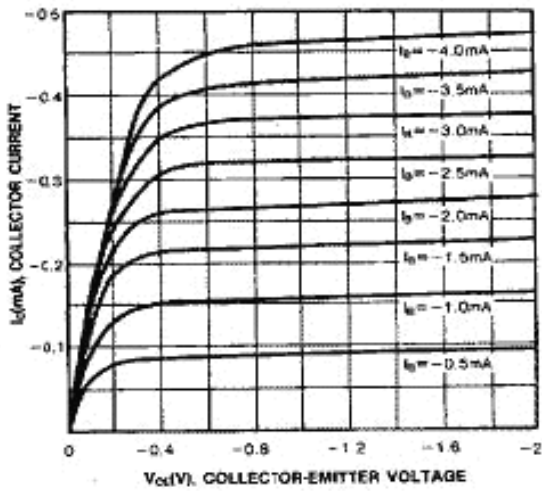
CLASSIFICATION OF hFE(2)

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

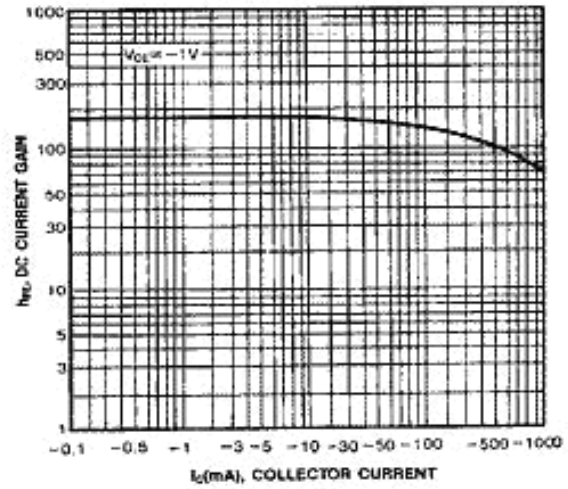
Typical Characteristics

SS8550

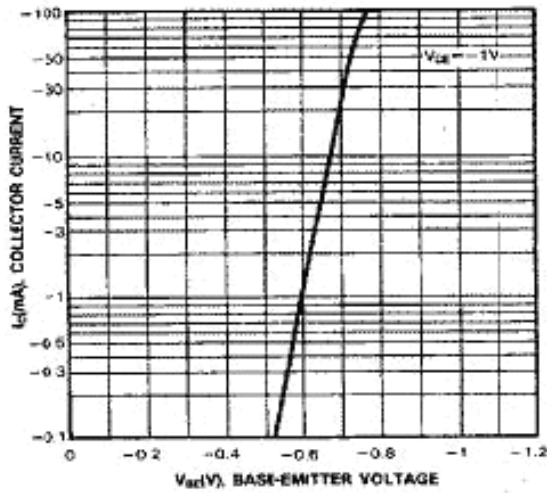
STATIC CHARACTERISTIC



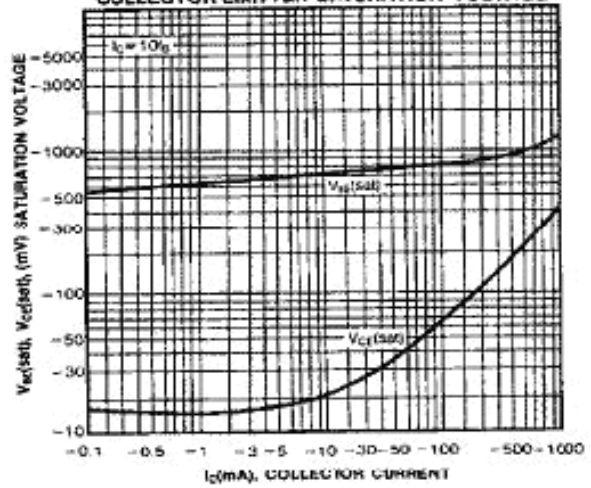
DC CURRENT GAIN



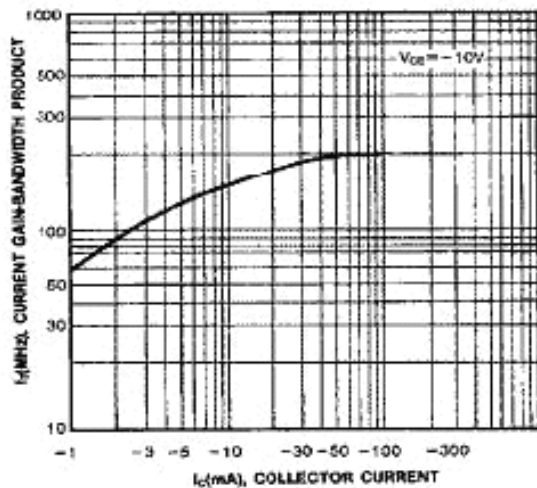
BASE-EMITTER ON VOLTAGE



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR OUTPUT CAPACITANCE

